Darlington Transistor





Features:

- Collector-Emitter sustaining voltage V_{CEO(sus)} = 80V (Min.) BDX33B, BDX34B
 = 100V (Minimum) BDX33C, BDX34C
- · Monolithic construction with Built-in Base-Emitter shunt resistor

Maximum Ratings

Characteristic	Symbol	BDX33B BDX34B	BDX33C BDX34C	Unit
Collector-Emitter Voltage	V _{CEO}	80	100	V
Collector-Base Voltage	V _{CBO}			
Emitter-Base Voltage	V _{EBO}	5		
Collector Current-Continuous -Peak	I _C I _{CM}	10 15		А
Base Current	I _B	0.25		
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	70 0.56		W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +150		°C

Thermal Characteristics

Characteristic	Symbol	Max.	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.78	°C/W



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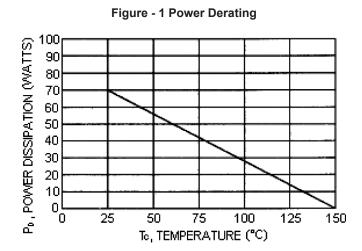


Electrical Characteristics:

(T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF Characteristics				
Collector-Emitter Sustaining Voltage (1) $I_C = 100 \text{mA}, I_B = 0$ BDX33B, BDX34B BDX33C, BDX34C	V _{CEO(sus)}	80 100	-	V
Collector Cut off Current $V_{CE} = 40V, I_{B} = 0 \qquad BDX33B, BDX34B$ $V_{CE} = 50V, I_{B} = 0 \qquad BDX33C, BDX34C$	I _{CEO}	-	0.5 0.5	mA
Collector-Base Cut off Current V_{CB} = Rated V_{CB} , I_{E} = 0	Ісво	-	200	μΑ
Emitter-Base Cut off Current $V_{EB} = 5V$, $I_{C} = 0$	I _{EBO}	-	10	mA
ON Characteristics (1)				
DC Current Gain $I_C = 3A$, $V_{CE} = 3V$ BDX33B/33C/34B/34C	h _{FE}	750	-	-
Collector-Emitter Saturation Voltage I _C = 3A, I _B = 6mA BDX33B/33C/34B/34C	V _{CE(sat)}	-	2.5	V
Base-Emitter On Voltage I _C = 3A, V _{CE} = 3V BDX33B/33C/34B/34C	V _{BE(on)}	-	2.5	V

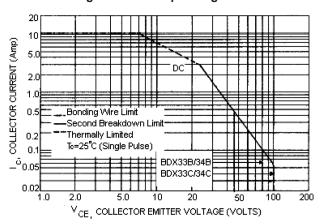
(1) Pulse Test: Pulse Width = 300µs, Duty Cycle ≤2%



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Figure - 2 Safe Operating Area



Pin Configuration:

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector(Case)

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate $I_{\rm C}\text{-}V_{\rm CE}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves

The data of Figure - 2 is based on $T_{J(PK)}$ = 150°C; TC is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)}$ <150°C. At high case temperatures, thermal limitation will reduce the power that can handled to values less than the limitations imposed by second breakdown.

Dimensions	Min.	Max.
А	14.68	15.31
В	9.78	10.42
С	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
Н	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.2	2.97
L	0.33	0.55
M	2.48	2.98
0	3.7	3.9

Dimensions: Millimetres

Part Number Table

Description	Part Number	
Darlington Transistor, TO-220	BDX33B	
	BDX33C	
	BDX34B	
	BDX34C	

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